

ETCHING METHOD AND ETCHING APPARATUS

ABSTRACT

An etching method includes a first storage process of supplying a first etching gas to a first gas supply path and storing the first etching gas in a first storage to increase an internal pressure of the first storage, a second storage process of supplying a second etching gas to a second gas supply path and storing the second etching gas in a second storage to increase an internal pressure of the second storage, a first supply process of supplying the first etching gas from the first storage into the processing container in a first period, and a second supply process of supplying the second etching gas from the second storage into the processing container in a second period, wherein at least one of a start point or an end point of the second period is set to be different from that of the first period.

(Fig. 2)